

chamber and are configured to introduce said inert gas and said vapor into said chamber in a same direction.--

REMARKS

By this amendment, Applicants cancel claims 4 and 8, without prejudice or disclaimer of the subject matter contained therein, propose amending claim 1 to more particularly claim the invention, and propose adding claims 21-23. No new matter has been added. Upon entry of this amendment, claims 1, 5, and 9-23 will remain pending, with claims 9-20 withdrawn from consideration as drawn to a nonelected invention.

In the last Office Action, the Examiner rejected claims 1, 4-5, and 8 under 35 U.S.C. § 102(b) as anticipated by Japanese KOKAI publication number 3-13576 ("*Isaka*").

To anticipate a claim under 35 U.S.C. § 102, a single reference must disclose each claim element. Applicants respectfully traverse the Examiner's rejection of claim

1. Claim 1 recites, *inter alia*:

A method of generating ions, comprising: heating an ion source material composed of indium monoiodide (InI) at a temperature of not lower than 250°C and not higher than 380°C, to generate vapor of said indium monoiodide (InI); and generating indium (In) ions by discharging said vapor.

Isaka appears to disclose a method for ion irradiation. The apparatus irradiates granular indium triiodine (InI₃), preferably in the temperature range of 300-500 °C. The InI₃ is decomposed by arc discharge to form indium ions.

Claim 1, instead, recites, "A method of generating ions, comprising: heating an ion source material composed of indium monoiodide (InI) *at a temperature of not lower than 250°C and not higher than 380°C*, to generate vapor of said indium monoiodide

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(InI); and generating indium (In) ions by discharging said vapor," which is different from the disclosure of *Isaka*. Therefore claim 1 should be allowed. Claims 5 and 21 should likewise be allowed, at least because of their dependence from allowable claim 1.

New claim 22 recites, *inter alia*:

A method of generating ions, comprising: . . . generating indium (In) ions by discharging said vapor in an arc chamber, wherein a filament is provided on one side surface of said arc chamber, and a reflecting counter electrode is provided on the other side surface of said arc chamber opposite to said one side surface.

Although *Isaka* appears to disclose a discharge chamber including a filament 51. *Isaka*, however, fails to disclose, at least, "a filament is provided on one side surface of said arc chamber, and a reflecting counter electrode is provided on the other side surface of said arc chamber opposite to said one side surface" as recited in claim 1. Absent a disclosure of each claim element, claim 22 is allowable over *Isaka*.

Claim 23 recites, *inter alia*:

A method of generating ions, comprising: . . . generating indium (In) ions by discharging said vapor in an arc chamber, wherein two gas inlets for an inert gas and said vapor are provided on the same face of the arc chamber and are configured to introduce said inert gas and said vapor into said chamber in the same direction.

Although *Isaka* appears to disclose a gas inlet for Argon 54 and an inlet for gasified indium iodide, it fails to disclose, at least, "two gas inlets for an inert gas and said vapor are provided *on the same face of the arc chamber* and are configured to *introduce said inert gas and said vapor into said chamber in the same direction*," as recited by claim 1. Absent a disclosure of each claim element, claim 23 is allowable over *Isaka*.

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Applicants respectfully request that this Amendment under 37 C.F.R. § 1.116 be entered by the Examiner, placing claims 1, 5, and 21–23 in condition for allowance. Applicants submit that the proposed amendment of claim 1 does not raise new issues or necessitate the undertaking of any additional search of the art by the Examiner, since all of the elements and their relationships claimed were either earlier claimed or inherent in the claims as examined. Therefore, this Amendment should allow for immediate action by the Examiner.

Furthermore, it is respectfully submitted that the entering of the Amendment would allow the Applicants to reply to the final rejections and place the application in condition for allowance. Finally, Applicants submit that the entry of the amendment would place the application in better form for appeal, should the Examiner dispute the patentability of the pending claims.

In view of the foregoing remarks, Applicants submit that this claimed invention is neither anticipated nor rendered obvious in view of the references cited against this application. Applicants therefore request the entry of this Amendment, the Examiner's reconsideration and reexamination of the application, and the timely allowance of the pending claims.

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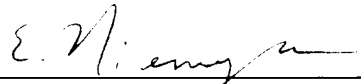
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Please grant any extensions of time required to enter this response and charge
any additional required fees to our deposit account 06-0916.

Respectfully submitted,

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Dated: September 20, 2002

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APPENDIX

1. (Twice Amended) A method of generating ions, comprising:

heating an ion source material composed of indium [iodide] monoiodide (InI)
whose particle size is generally larger than a diameter of an oven nozzle and in a range
of heating temperature to produce a desired an ion beam current effective [,] to
generate vapor of said indium [iodide] monoiodide (InI); and
generating indium (In) ions by discharging said vapor.

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